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\*\* CONTINUING DATA \*\*\*\*\*

None

\*\* FOREIGN APPLICATIONS \*\*\*\*\*

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IF REQUIRED, FOREIGN FILING LICENSE GRANTED

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Foreign Priority claimed 35 USC 119 (a-d) conditions met Verified and Acknowledged	<input checked="" type="checkbox"/> yes <input type="checkbox"/> no <input checked="" type="checkbox"/> yes <input type="checkbox"/> no <input type="checkbox"/> Met after Allowance Examiner's Signature <i>[Signature]</i> Initials <i>[Initials]</i>	STATE OR COUNTRY KOREA, REPUBLIC OF	SHEETS DRAWING 3	TOTAL CLAIMS 37	INDEPENDENT CLAIMS 2
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## TITLE

Method of fabricating a mos transistor with elevated source/drain structure using a selective epitaxial growth process

☐ All Fees